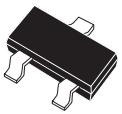
查询CMPT6427供应商

CMPT6427

NPN SILICON DARLINGTON TRANSISTOR



SOT-23 CASE

Central™ Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT6427 type is a NPN Silicon Darlington Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.
Marking Code is C1V.

MAXIMUM RATINGS (T_A=25°C)

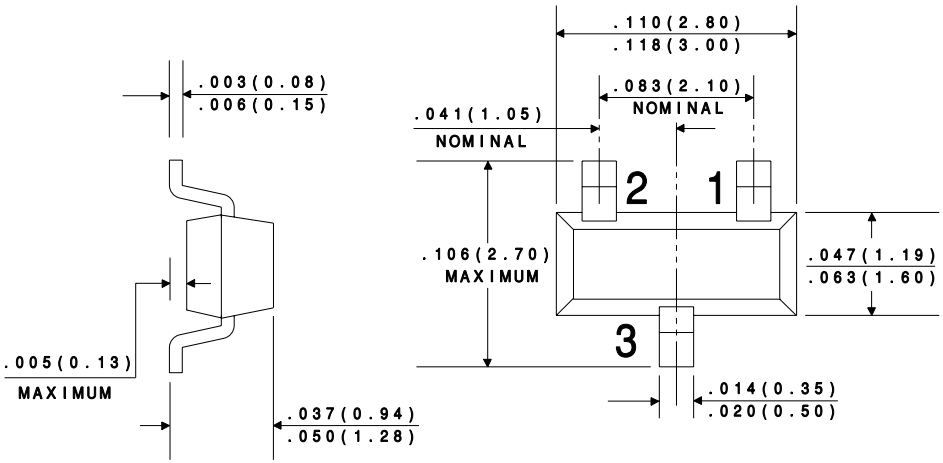
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	12	V
Collector Current	I_C	500	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	V_{CB}=30V		50	nA
I_{CEO}	V_{CE}=25V		1.0	μA
I_{EBO}	V_{BE}=10V		50	nA
BV_{CBO}	I_C=100μA	40		V
BV_{CEO}	I_C=10mA	40		V
BV_{EBO}	I_E=10μA	12		V
$V_{CE(SAT)}$	I_C=50mA, I_B=0.5mA		1.20	V
$V_{CE(SAT)}$	I_C=500mA, I_B=0.5mA		1.50	V
$V_{BE(SAT)}$	I_C=500mA, I_B=0.5mA		2.00	V
$V_{BE(ON)}$	V_{CE}=5.0V, I_C=50mA		1.75	V
h_{FE}	V_{CE}=5.0V, I_C=10mA	10K	100K	
h_{FE}	V_{CE}=5.0V, I_C=100mA	20K	200K	
h_{FE}	V_{CE}=5.0V, I_C=500mA	14K	140K	
f_T	V_{CE}=5.0V, IC=10mA, f=100MHz	130		MHz

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz		7.0	pF
C_{ib}	V_{BE}=0.5V, I_C=0, f=1.0MHz		15	pF
N_F	V_{CE}=5.0V, I_C=1.0mA, R_S=100kΩ, f=1.0kHz TO 15.7kHz		10	dB

All dimensions in inches (mm).



LEAD CODE:

1) BASE
2) EMITTER
3) COLLECTOR

R2